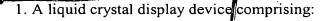
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What is claimed is:



- a first substrate with a pixel area
- a first electrode pattern on the first substrate, wherein the first electrode pattern includes an edge;

an insulating layer over the first electrode pattern;

a second electrode pattern over the insulating layer, wherein the second electrode pattern includes at least two conductive members;

a short-prevention member on the insulating layer, above the edge, and between the at least two conductive members; and

a pixel electrode in the pixel area;

wherein the short-prevention member prevents electric shorts between the at least two conductive members caused by residual material that extends along the edge.

- 2. The liquid crystal display device of claim 1, wherein the first electrode pattern includes a gate line, a gate electrode and a lower electrode of a storage capacitor.
- 3. The liquid crystal display device of claim 1, wherein the second electrode pattern comprises a data line, a source electrode, a drain electrode and an upper electrode of a storage capacitor.
- 4. The liquid crystal display device of claim 1, wherein the insulating layer forms a gate insulating layer.
 - 5. The liquid crystal display device of claim 4, further comprising:

- a gate electrode under the gate insulating layer;
- a semiconductor layer on the gate insulating layer and over the gate electrode; and source and drain electrodes over the semiconductor layer.
- 6. The liquid crystal display device of claim 1, wherein the short-prevention member is formed at a same time as the semiconductor layer.
 - 7. The liquid crystal display device of claim 1, wherein the short-prevention member is comprised of a same material as the semiconductor layer.
 - 8. The liquid crystal display device of claim 1, further comprising:
 - a lower electrode; and

an upper electrode,

wherein the lower electrode and the upper electrode are separated by the insulating

- layer.
- 9. The liquid crystal display device of claim 1, wherein the short-prevention member is formed as an island.
- 20 10. The liquid crystal display device of claim 1, further including:
 - a second substrate adjacent the first substrate; and
 - a liquid crystal between the first substrate and the second substrate.
 - 11. A liquid crystal display device comprising:
- a gate pattern on a first substrate, the gate pattern including a gate line and a gate

electrode;

an insulating layer over the first substrate and the gate pattern;

- a semiconductor layer on the insulating layer and over the gate electrode;
- a short-prevention member on the insulating layer and over an edge of the gate
- 5 pattern;
- a data pattern including a data line and source and drain electrodes,
- a pixel electrode electrically connected to the drain electrode;
- 12. The liquid crystal display device of claim 11, wherein the gate electrode, insulating layer, semiconductor layer, source/drain electrodes are parts of a thin film transistor.
- 13. The liquid crystal display device of claim 12, wherein the thin film transistor is formed at a crossing of the gate line and the data line.
- 14. The liquid crystal display device of claim 13, wherein the short-prevention member is formed at a same time as the semiconductor layer.
- 15. The liquid crystal display device of claim 14, wherein the short-prevention member is formed of a same material as the semiconductor layer.
 - 16. The liquid crystal display device of claim 11, further comprising a storage capacitor, wherein the gate line forms a lower electrode and wherein the data pattern further forms an upper electrode, of the storage capacitor.

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- 17. The liquid crystal display device of claim 11, wherein the short-prevention member is an island.
 - 18. The liquid crystal display device of claim 11, further including:
 - a second substrate adjacent the first substrate; and
 - a liquid crystal layer between the first and second substrates.
- 19. A method of fabricating a liquid crystal display device, comprising:

 forming a first electrode pattern on a first substrate having a pixel area;

 forming an insulating layer over the first substrate and over the first electrode

 pattern;

forming a short-prevention member on the insulating layer and over an edge of the first electrode pattern;

forming a second electrode pattern on the insulating layer; and forming a pixel electrode in the pixel area;

wherein the short-prevention member is disposed to prevent electric shorts in the second electrode pattern.

- 20. The method of claim 19, wherein the first electrode pattern is formed using a wet etch process, and wherein the first electrode pattern includes a gate line, a gate electrode, and a lower electrode of a storage capacitor
- 21. The method of claim 19, wherein the second electrode pattern is formed using a wet etch process, and wherein the second electrode pattern includes a data line, source/drain electrodes, and an upper electrode of a storage capacitor.

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- 22. The method of claim 20, further comprising:

 forming a gate electrode under the insulating layer;

 forming a semiconductor layer over the insulating layer; and

 forming source/drain electrodes over the semiconductor layer.
- 23. The method of claim 22, wherein the shorf-prevention member is formed of a same material as the semiconductor layer.
- 24. The method of claim 19, wherein the short-prevention member is formed as an island.
- 25. The method of claim 19, wherein the short-prevention layer is formed by dry etching.
 - 26. A method of fabricating a liquid crystal display device, comprising:

forming a gate pattern on a first substrate, wherein the gate pattern includes a gate line, a gate electrode, and a lower electrode;

forming an insulating layer over the first substrate and over the gate pattern;

forming a semiconductor layer on the insulating layer and over the gate electrode,

forming a short-prevention member on the insulating layer and over an edge of the
gate pattern;

forming a data pattern, including a data line, source/drain electrodes, and an upper electrode; and

forming a pixel electrode having an electrical connection to the drain electrode.

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- 27. The method of claim 26, wherein the short-prevention member is formed of a same material as the semiconductor layer.
- 28. The method of claim 26, wherein the short-prevention member is formed as an island.
 - 29. The method of claim 26, wherein the gate pattern is formed using a wet etch process.
 - 30. The method of claim 26, wherein the data pattern is formed using a wet etch process.
 - 31. The method of claim 26, wherein the semiconductor layer and short-prevention member are each formed using a dry etch process.
 - 32. The method of claim 26 further including disposing a second substrate adjacent the first substrate.
- 33. The method of claim 26, further including disposing a liquid crystal between the first substrate and the second substrate.